Supplementary Information

Triethanolamine Doped Multilayer MoS\textsubscript{2} Field Effect Transistors

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Figure S1 Distribution of mobility ratio (a), contact resistance ($R_C$) ratio (b), subthreshold swing (SS) ratio (c) and threshold voltage ($V_{th}$) shift (d) before and after the doping process.
Figure. S2 Stability of on-current ($I_{on}$) (a), threshold voltage ($V_{th}$) (b), subthreshold swing (SS) (c) and contact resistance ($R_C$) (d) in air for 3 days before and after the doping process.

Figure. S3 (a) AFM image of multilayer MoS$_2$. (b) Height profile measured along the green line in figure S3(a).